

TENTATIVE

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74VCX14FT

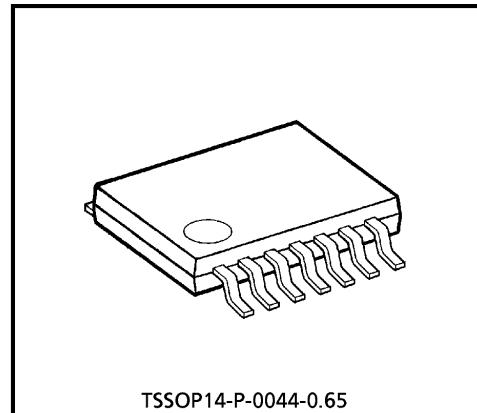
LOW-VOLTAGE HEX SCHMITT INVERTER WITH 3.6 V TOLERANT INPUTS AND OUTPUTS

The TC74VCX14FT is a high performance CMOS schmitt inverter. Designed for use in 1.8, 2.5 or 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

Pin configuration and function are the same as the TC74VCX04 but the inputs have hysteresis and with its schmitt trigger function, the TC74VCX14 can be used as a line receivers which will receive slow input signals.

All inputs are equipped with protection circuits against static discharge.



TSSOP14-P-0044-0.65

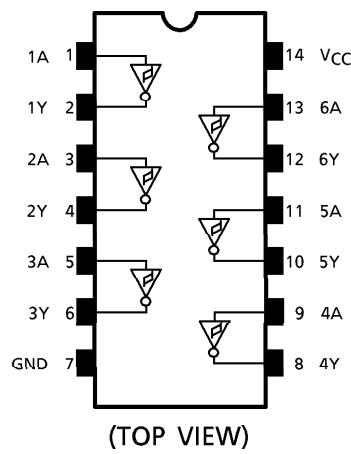
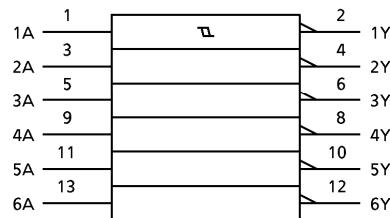
Weight : 0.06 g (Typ.)

FEATURES

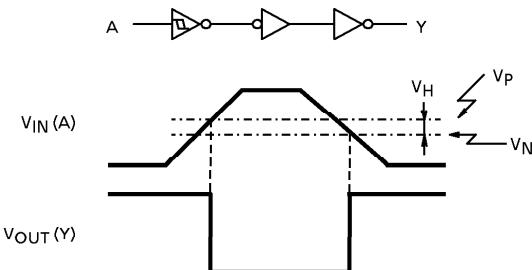
- Low voltage operation : $V_{CC} = 1.8\sim 3.6 \text{ V}$
- High speed operation : $t_{pd} = \text{TBD} (\text{max})$ at $V_{CC} = 3.0\sim 3.6 \text{ V}$
 $t_{pd} = \text{TBD} (\text{max})$ at $V_{CC} = 2.3\sim 2.7 \text{ V}$
 $t_{pd} = \text{TBD} (\text{max})$ at $V_{CC} = 1.8 \text{ V}$
- Output current : $I_{OH}/I_{OL} = \pm 24 \text{ mA} (\text{min})$ at $V_{CC} = 3.0 \text{ V}$
 $I_{OH}/I_{OL} = \pm 18 \text{ mA} (\text{min})$ at $V_{CC} = 2.3 \text{ V}$
 $I_{OH}/I_{OL} = \pm 6 \text{ mA} (\text{min})$ at $V_{CC} = 1.8 \text{ V}$
- Latch-up performance : $\pm 300 \text{ mA}$
- ESD performance : Human body model $> \pm 2000 \text{ V}$
Machine model $> \pm 200 \text{ V}$
- Package : TSSOP
(Thin Shrink Small Outline Package)
- Power down protection is provided on all inputs and outputs.

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PIN ASSIGNMENT**IEC LOGIC SYMBOL****TRUTH TABLE**

INPUTS	OUTPUTS
A	Y
L	H
H	L

SYSTEM DIAGRAM, WAVEFORM**MAXIMUM RATINGS**

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V _{CC}	- 0.5~4.6	V
DC Input Voltage	V _{IN}	- 0.5~4.6	V
DC Output Voltage	V _{OUT}	- 0.5~4.6 (Note 1)	V
		- 0.5~V _{CC} + 0.5 (Note 2)	
Input Diode Current	I _{IK}	- 50	mA
Output Diode Current	I _{OK}	± 50 (Note 3)	mA
DC Output Current	I _{OUT}	± 50	mA
Power Dissipation	P _D	180	mW
DC V _{CC} / Ground Current	I _{CC} / I _{GND}	± 100	mA
Storage Temperature	T _{stg}	- 65~150	°C

(Note 1) : V_{CC} = 0 V(Note 2) : High or Low State. I_{OUT} absolute maximum rating must be observed.(Note 3) : V_{OUT} < GND, V_{OUT} > V_{CC}

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	1.8~3.6	V
		1.2~3.6 (Note 4)	
Input Voltage	V_{IN}	-0.3~3.6	V
Output Voltage	V_{OUT}	0~3.6 (Note 5)	V
		0~ V_{CC} (Note 6)	
Output Current	I_{OH} / I_{OL}	± 24 (Note 7)	mA
		± 18 (Note 8)	
		± 6 (Note 9)	
Operating Temperature	T_{opr}	-40~85	°C

(Note 4) : Data Retention Only

(Note 5) : $V_{CC} = 0$ V

(Note 6) : High or Low State

(Note 7) : $V_{CC} = 3.0\sim 3.6$ V(Note 8) : $V_{CC} = 2.3\sim 2.7$ V(Note 9) : $V_{CC} = 1.8$ V

ELECTRICAL CHARACTERISTICS

DC characteristics ($T_a = -40\sim 85^\circ\text{C}$, $2.7\text{ V} < V_{CC} \leq 3.6\text{ V}$)

PARAMETER	SYMBOL	TEST CONDITION		V_{CC} (V)	MIN	MAX	UNIT	
Input Voltage	"H" Level	V_P		3.6	—	TBD	V	
	"L" Level			3.0	—	TBD		
	"H" Level	V_{IN}		3.6	TBD	—		
	"L" Level			3.0	TBD	—		
Hysteresis Voltage		V_H		3.6	TBD	TBD	V	
				3.0	TBD	TBD		
Output Voltage	"H" Level	V_{OH}	$V_{IN} = V_{IL}$	$I_{OH} = -100\text{ }\mu\text{A}$	2.7~3.6	$V_{CC} - 0.2$	V	
	"H" Level			$I_{OH} = -12\text{ mA}$	2.7	2.2		
	"H" Level			$I_{OH} = -18\text{ mA}$	3.0	2.4		
	"H" Level			$I_{OH} = -24\text{ mA}$	3.0	2.2		
	"L" Level	V_{OL}	$V_{IN} = V_{IH}$	$I_{OL} = 100\text{ }\mu\text{A}$	2.7~3.6	—	V	
				$I_{OL} = 12\text{ mA}$	2.7	—		
				$I_{OL} = 18\text{ mA}$	3.0	—		
				$I_{OL} = 24\text{ mA}$	3.0	—		
Input Leakage Current	I_{IN}	$V_{IN} = 0\sim 3.6\text{ V}$		2.7~3.6	—	± 5.0	μA	
Power Off Leakage Current	I_{OFF}	$V_{IN}, V_{OUT} = 0\sim 3.6\text{ V}$		0	—	10.0	μA	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND		2.7~3.6	—	20.0	μA	
		$V_{CC} \leq V_{IN} \leq 3.6\text{ V}$		2.7~3.6	—	± 20.0		
Increase In I_{CC} Per Input	ΔI_{CC}	$V_{IH} = V_{CC} - 0.6\text{ V}$		2.7~3.6	—	750	μA	

DC characteristics ($T_a = -40\sim85^\circ C$, $2.3 V \leq V_{CC} \leq 2.7 V$)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN	MAX	UNIT	
Input Voltage	"H" Level	V_P	$V_{IN} = V_{IL}$	$I_{OH} = -100 \mu A$	2.3	—	TBD	V	
	"L" Level	V_N			2.3	TBD	—		
Hysteresis Voltage		V_H			2.3	TBD	TBD	V	
Output Voltage	"H" Level	V_{OH}	$V_{IN} = V_{IL}$	$I_{OH} = -100 \mu A$	2.3~2.7	$V_{CC} - 0.2$	—	V	
				$I_{OH} = -6 mA$	2.3	2.0	—		
				$I_{OH} = -12 mA$	2.3	1.8	—		
				$I_{OH} = -18 mA$	2.3	1.7	—		
	"L" Level	V_{OL}	$V_{IN} = V_{IH}$	$I_{OL} = 100 \mu A$	2.3~2.7	—	0.2		
				$I_{OL} = 12 mA$	2.3	—	0.4		
Input Leakage Current		I_{IN}	$V_{IN} = 0\sim3.6 V$		2.3~2.7	—	± 5.0	μA	
Power Off Leakage Current		I_{OFF}	$V_{IN}, V_{OUT} = 0\sim3.6 V$		0	—	10.0	μA	
Quiescent Supply Current		I_{CC}	$V_{IN} = V_{CC}$ or GND		2.3~2.7	—	20.0	μA	
			$V_{CC} \leq V_{IN} \leq 3.6 V$		2.3~2.7	—	± 20.0		

DC characteristics ($T_a = -40\sim85^\circ C$, $1.8 V \leq V_{CC} < 2.3 V$)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN	MAX	UNIT	
Input Voltage	"H" Level	V_P	$V_{IN} = V_{IL}$	$I_{OH} = -100 \mu A$	1.8	—	TBD	V	
	"L" Level	V_N			1.8	TBD	—		
Hysteresis Voltage		V_H			1.8	TBD	TBD	V	
Output Voltage	"H" Level	V_{OH}	$V_{IN} = V_{IL}$	$I_{OH} = -100 \mu A$	1.8	$V_{CC} - 0.2$	—	V	
				$I_{OH} = -6 mA$	1.8	1.4	—		
				$I_{OL} = 100 \mu A$	1.8	—	0.2		
				$I_{OL} = 6 mA$	1.8	—	0.3		
Input Leakage Current		I_{IN}	$V_{IN} = 0\sim3.6 V$		1.8	—	± 5.0	μA	
Power Off Leakage Current		I_{OFF}	$V_{IN}, V_{OUT} = 0\sim3.6 V$		0	—	10.0	μA	
Quiescent Supply Current		I_{CC}	$V_{IN} = V_{CC}$ or GND		1.8	—	20.0	μA	
			$V_{CC} \leq V_{IN} \leq 3.6 V$		1.8	—	± 20.0		

AC characteristics ($T_a = -40\sim85^\circ C$, Input $t_r = t_f = 2.0 \text{ ns}$, $C_L = 30 \text{ pF}$, $R_L = 500 \Omega$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC} (\text{V})$	MIN	MAX	UNIT
			1.8			
Propagation Delay Time	t_{pLH} t_{pHL}	(Fig. 1, 2)	2.5 \pm 0.2	0.8	TBD	ns
			3.3 \pm 0.3	0.6	TBD	
			1.8	—	0.5	
Output To Output Skew	t_{osLH} t_{osHL}	(Note 10)	2.5 \pm 0.2	—	0.5	ns
			3.3 \pm 0.3	—	0.5	

For $C_L = 50 \text{ pF}$, add approximately 300 ps to the AC maximum specification.

(Note 10) : Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLhn}|, t_{osHL} = |t_{pHlm} - t_{pHln}|)$$

Dynamic switching characteristics ($T_a = 25^\circ C$, Input $t_r = t_f = 2.0 \text{ ns}$, $C_L = 30 \text{ pF}$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC} (\text{V})$	TYP.	UNIT
			1.8		
Quiet Output Maximum Dynamic V_{OL}	V_{OLP}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	1.8	0.25	V
		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	2.5	0.6	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	3.3	0.8	
Quiet Output Minimum Dynamic V_{OL}	V_{OLV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	1.8	-0.25	V
		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	2.5	-0.6	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	3.3	-0.8	
Quiet Output Minimum Dynamic V_{OH}	V_{OHV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	1.8	1.5	V
		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	2.5	1.9	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	3.3	2.2	

(Note 11) : Parameter guaranteed by design.

Capacitive characteristics ($T_a = 25^\circ C$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC} (\text{V})$	TYP.	UNIT
			1.8, 2.5, 3.3		
Input Capacitance	C_{IN}		6	pF	
Power Dissipation Capacitance	C_{PD}	$f_{IN} = 10 \text{ MHz}$ (Note 12)	20	pF	

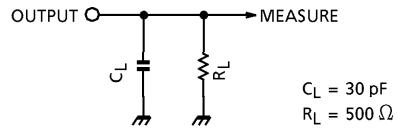
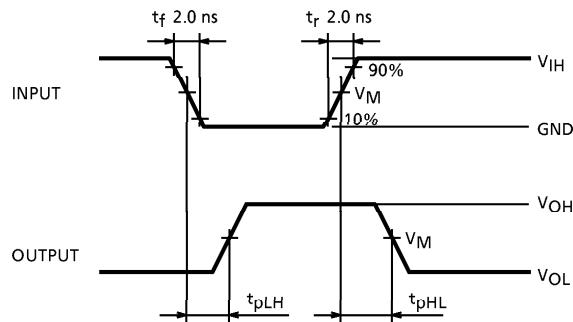
(Note 12) : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(\text{opr.})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 \text{ (Per gate)}$$

TEST CIRCUIT

Fig.1

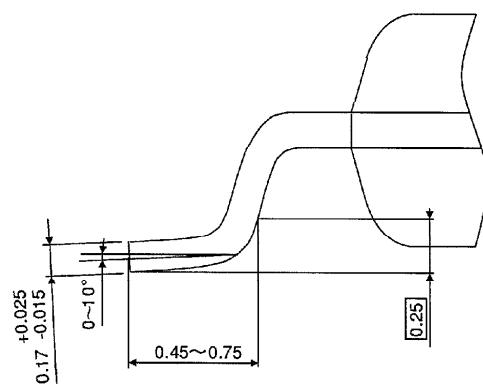
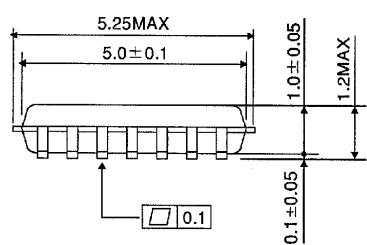
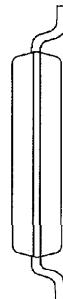
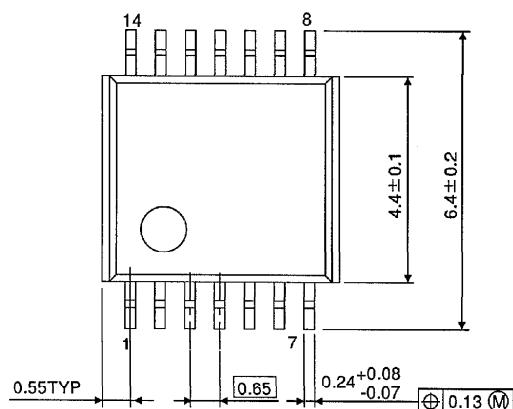
**AC WAVEFORM**Fig.2 t_{pLH} , t_{pHL} 

SYMBOL	V_{CC}		
	$3.3 \pm 0.3 \text{ V}$	$2.5 \pm 0.2 \text{ V}$	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$

OUTLINE DRAWING

TSSOP14-P-0044-0.65

Unit : mm



Weight : 0.06 g (Typ.)

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